

2021 10 27

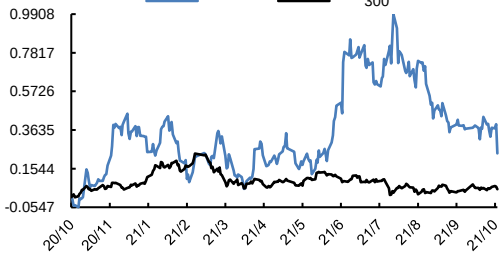
()

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2021Q3

+IDM

688396



300

	1M	3M	12M
300	-10.7%	-32.0%	23.7%
300	0.4%	3.1%	4.2%

2021/10/27

52

46.11-104.47

82,030.51

26,925.09

132,009.19

43,329.72

2,952.81

%

0.00

2021H1

*

*

2021-08-20

2020

IDM

*

*

2021-01-20

:

2021	2021	69.28	(
+41.70%)	16.84	(	+145.20%)
24.73	+35.43%	+2.60%	2021Q3
6.16	(	+117.26%	-7.73%)

■ 2021Q3

IDM

2021Q3

37.86%	+8.35pct	+1.59pct
24.60%	+7.57pct	-2.78pct
6.02%	+0.55pct	+3.48pct
1.53%	-0.09pct	+0.09pct
6.35%	+0.36pct	+2.35pct
+0.29pct	+1.04pct	-1.86%

■

12

2021Q3

2.20

+52.60%

MOSFET

1 MOSFET

MOSFET

2 IGBT

IGBT

IGBT

3

650V SiC JBS

SiC

MOSFET

2021M6

12

12

3

12

IDM

12

IDM
 MOSFET IGBT
 1.78/2.08/2.33 /
 5G
 23.49/27.46/30.80
 PE
 2021-2023
 EPS
 39/34/30

■

	2020	2021E	2022E	2023E
	6977	9321	10899	12310
	21	34	17	13
	964	2349	2746	3080
	140	144	17	12
	0.73	1.78	2.08	2.33
ROE(%)	9	18	18	16

Wind

688396					62.14					2021/10/27				

Wind

